

SHINDENGEN

VX-2 Series Power MOSFET

N-Channel Enhancement type

2SK2563

(F4F60VX2)

600V4A

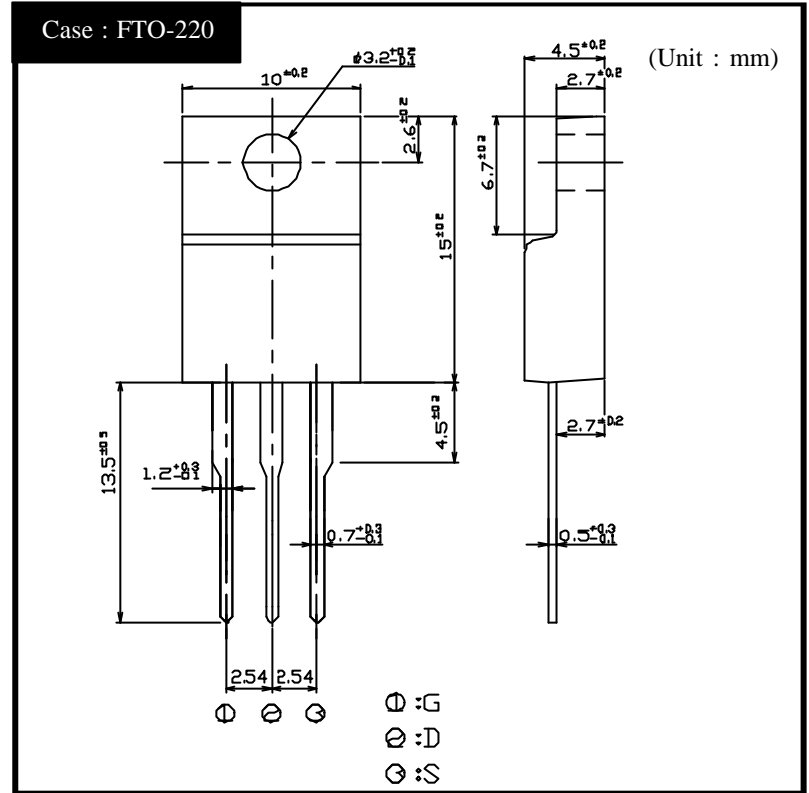
FEATURES

Input capacitance (Ciss) is small.
Especially, input capacitance at 0 bias is small.
The static Rds(on) is small.
The switching time is fast.
Avalanche resistance guaranteed.

APPLICATION

Switching power supply of
AC 100-200V input
Inverter
Power Factor Control Circuit

OUTLINE DIMENSIONS



RATINGS

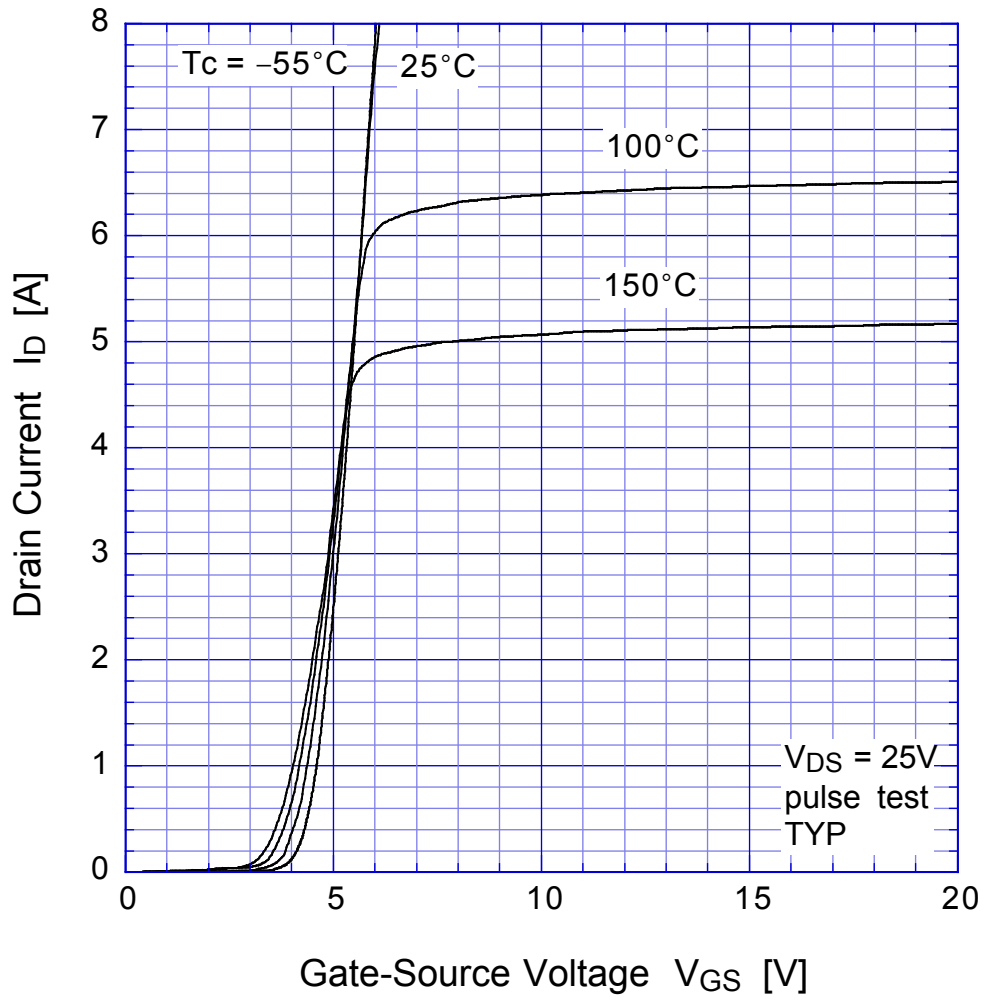
Absolute Maximum Ratings (Tc = 25 °C)

| Item | Symbol | Conditions | Ratings | Unit |
|---------------------------------|------------------|--------------------------------|-----------|------|
| Storage Temperature | T _{stg} | | -55 ~ 150 | |
| Channel Temperature | T _{ch} | | 150 | |
| Drain-Source Voltage | V _{DSS} | | 600 | V |
| Gate-Source Voltage | V _{GSS} | | ± 30 | |
| Continuous Drain Current (DC) | I _D | | 4 | A |
| Continuous Drain Current (Peak) | I _{DP} | | 12 | |
| Continuous Source Current (DC) | I _S | | 4 | |
| Total Power Dissipation | P _T | | 30 | W |
| Single Pulse Avalanche Current | I _{AS} | T _{ch} = 25 | 4 | A |
| Dielectric Strength | V _{dis} | Terminals to case, AC 1 minute | 2 | kV |
| Mounting Torque | TOR | (Recommended torque : 0.3N·m) | 0.5 | N·m |

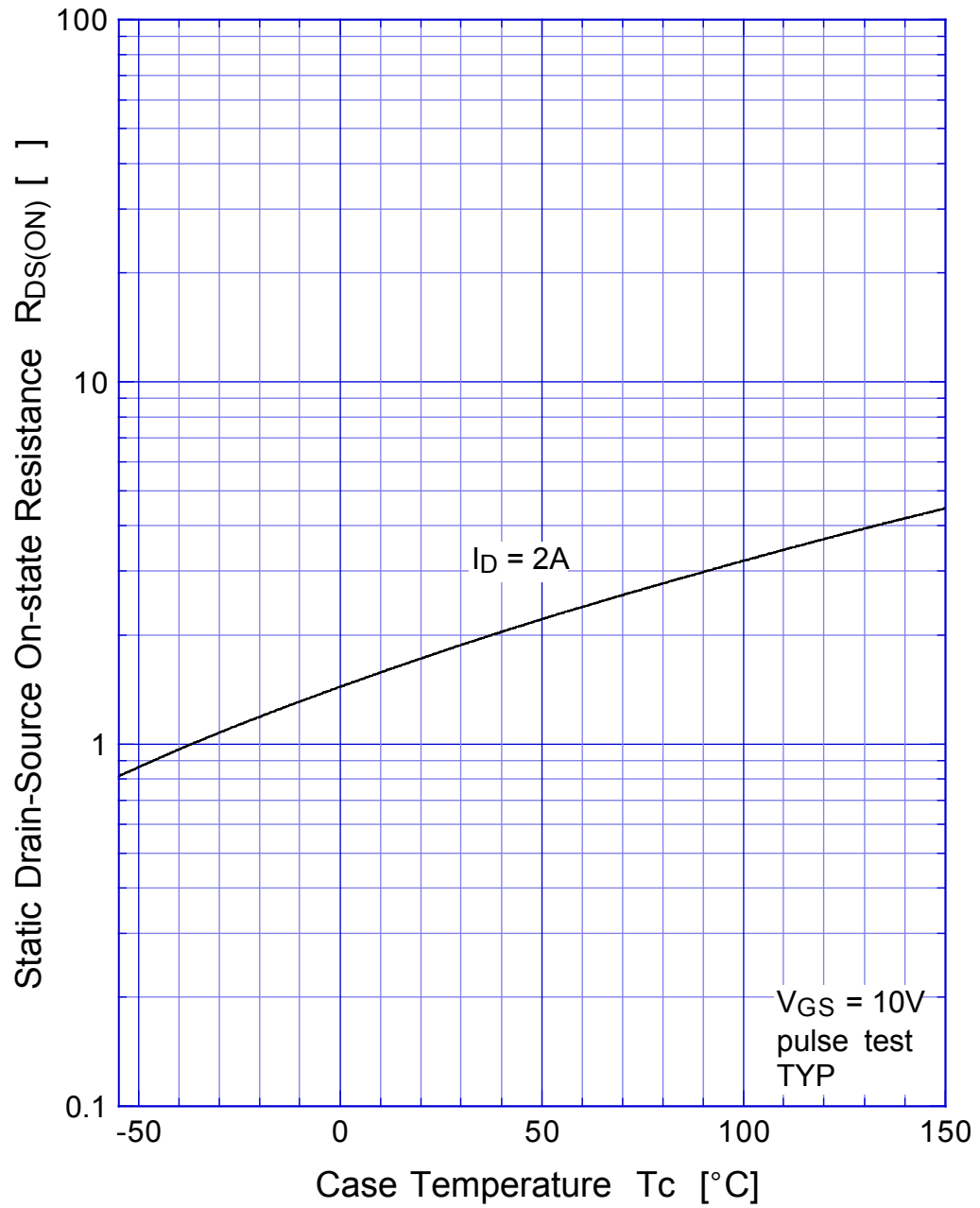
VX-2 Series Power MOSFET**2SK2563 (F4F60VX2)**●Electrical Characteristics $T_c = 25^\circ\text{C}$

| Item | Symbol | Conditions | Min. | Typ. | Max. | Unit |
|---|---------------|--|------|------|-----------|---------------------------|
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $I_D = 1\text{mA}, V_{GS} = 0\text{V}$ | 600 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$ | | | 250 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$ | | | ± 0.1 | |
| Forward Transconductance | g_{fs} | $I_D = 2\text{A}, V_{DS} = 10\text{V}$ | 1.5 | 3.8 | | S |
| Static Drain-Source On-state Resistance | $R_{DS(ON)}$ | $I_D = 2\text{A}, V_{GS} = 10\text{V}$ | | 1.8 | 2.2 | Ω |
| Gate Threshold Voltage | V_{TH} | $I_D = 1\text{mA}, V_{DS} = 10\text{V}$ | 2.5 | 3.0 | 3.5 | V |
| Source-Drain Diode Forwade Voltage | V_{SD} | $I_S = 2\text{A}, V_{GS} = 0\text{V}$ | | | 1.5 | |
| Thermal Resistance | θ_{jc} | junction to case | | | 4.16 | $^\circ\text{C}/\text{W}$ |
| Total Gate Charge | Q_g | $V_{DD} = 400\text{V}, V_{GS} = 10\text{V}, I_D = 4\text{A}$ | | 21 | | nC |
| Input Capacitance | C_{iss} | $V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$ | | 540 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 40 | | |
| Output Capacitance | C_{oss} | | | 120 | | |
| Turn-On Time | t_{on} | $I_D = 2\text{A}, R_L = 75\Omega, V_{GS} = 10\text{V}$ | | 28 | 40 | ns |
| Turn-Off Time | t_{off} | | | 110 | 160 | |

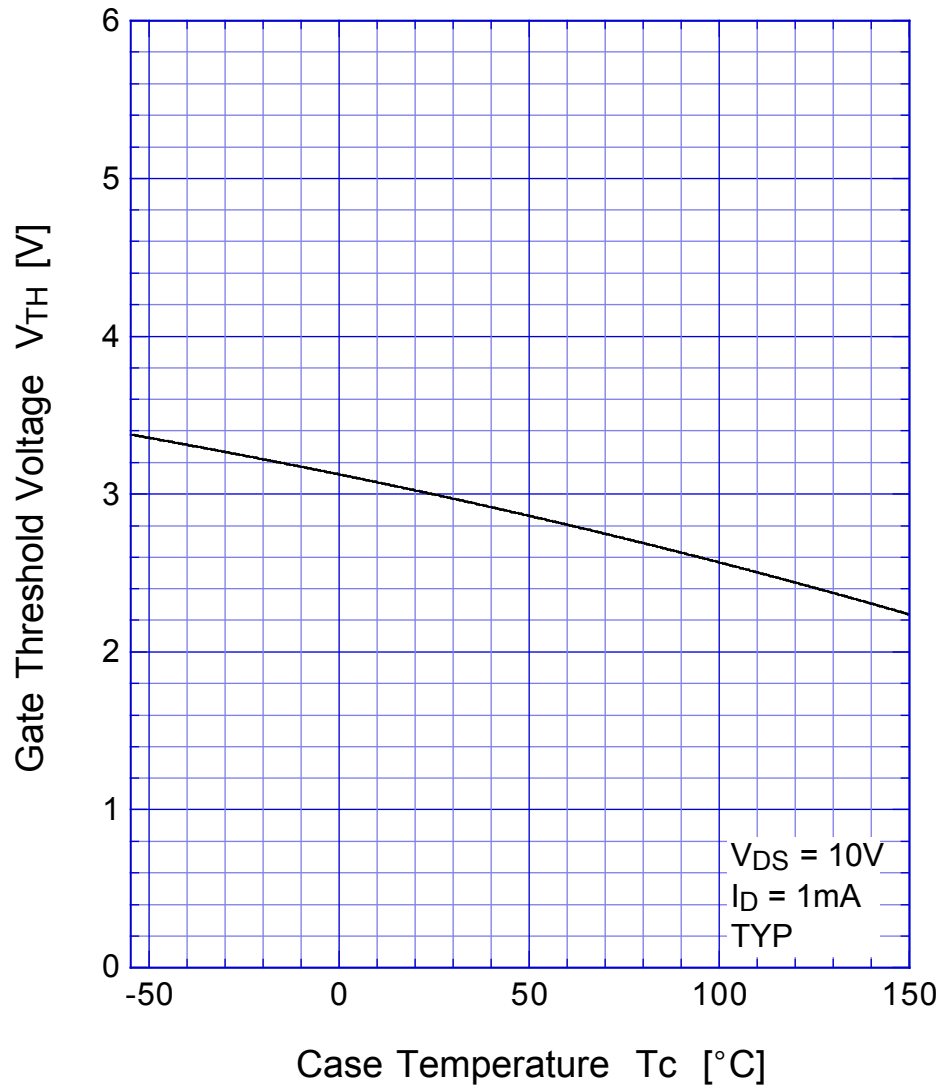
2SK2563 Transfer Characteristics



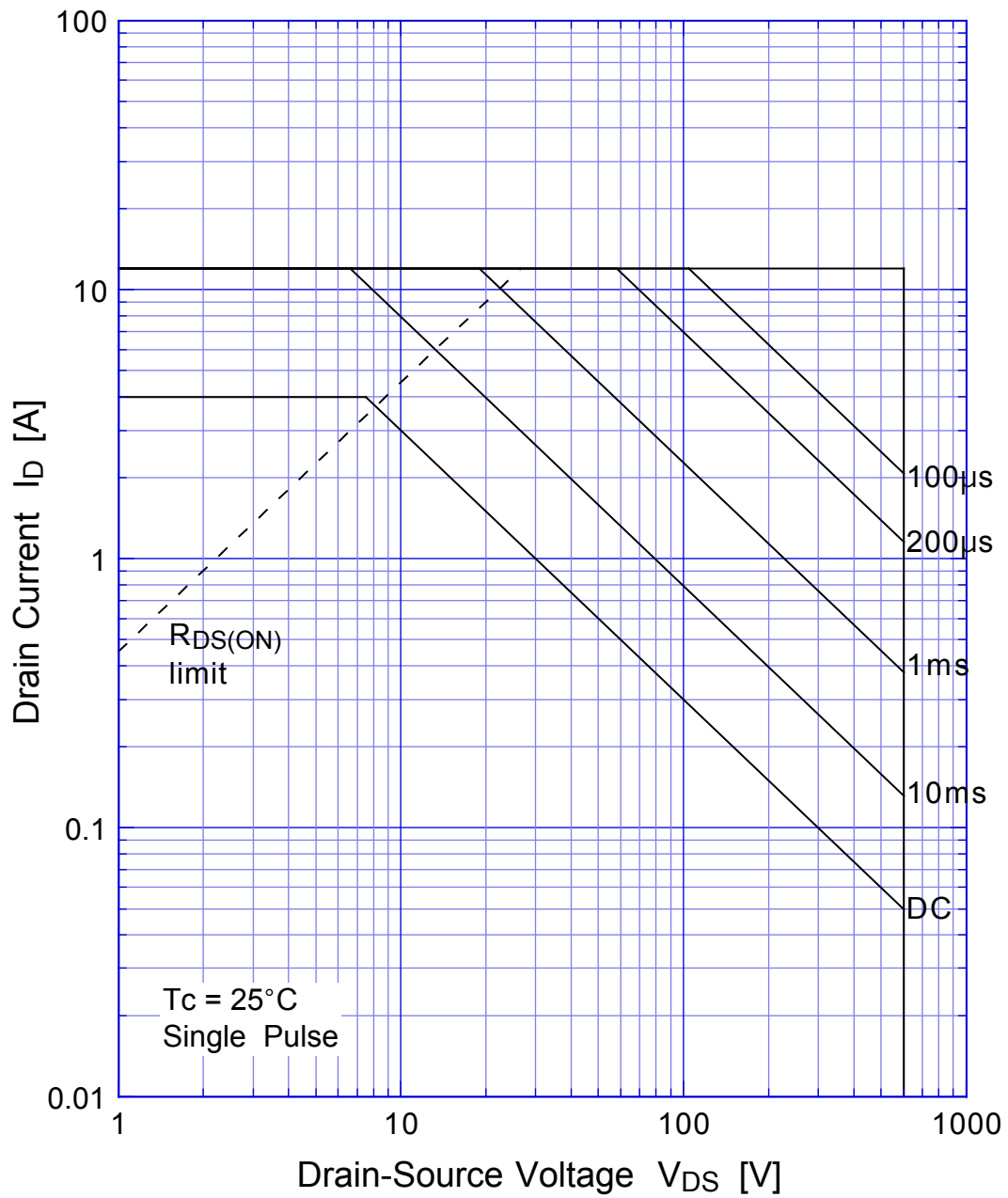
2SK2563 Static Drain-Source On-state Resistance



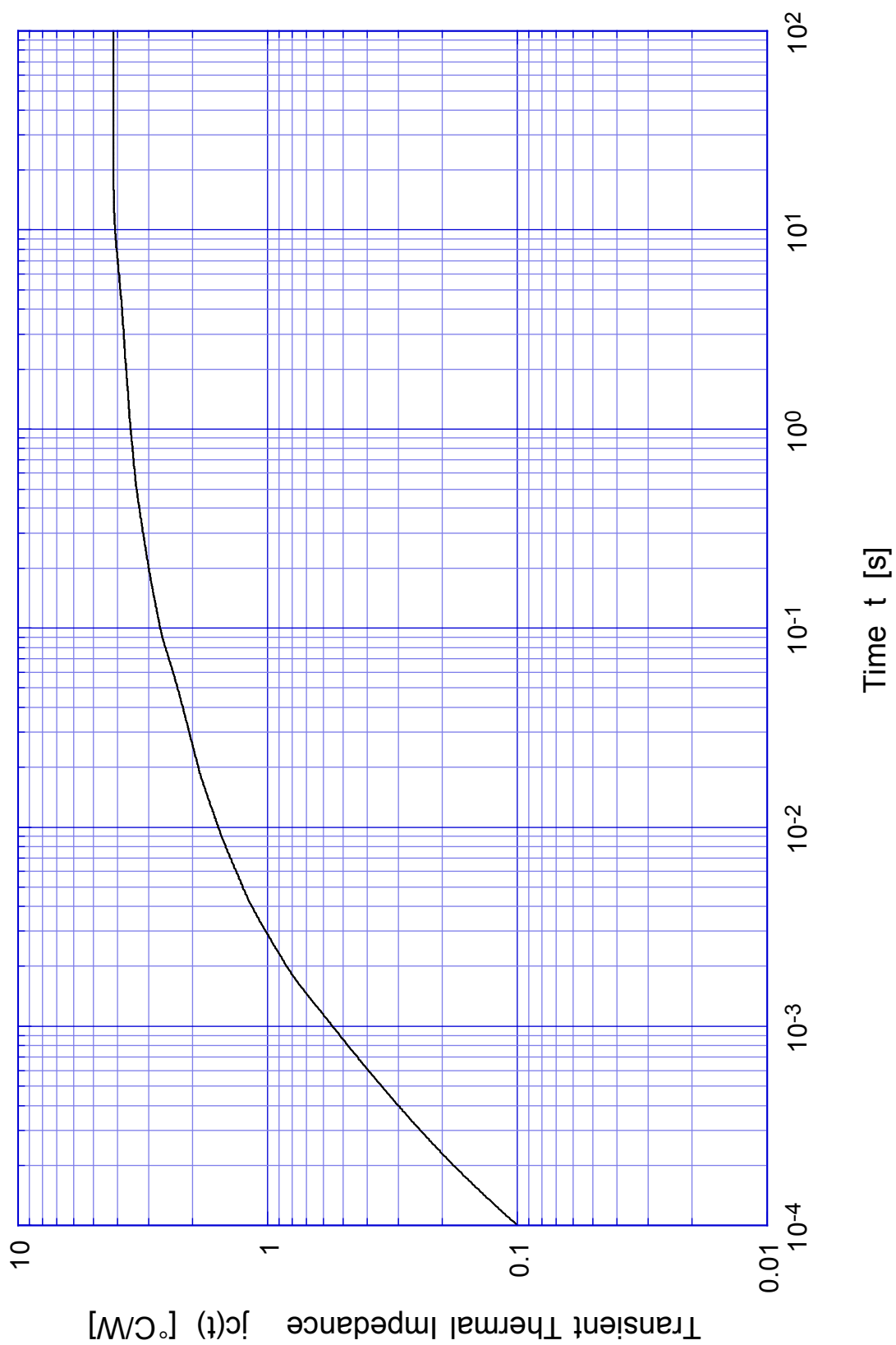
2SK2563 Gate Threshold Voltage



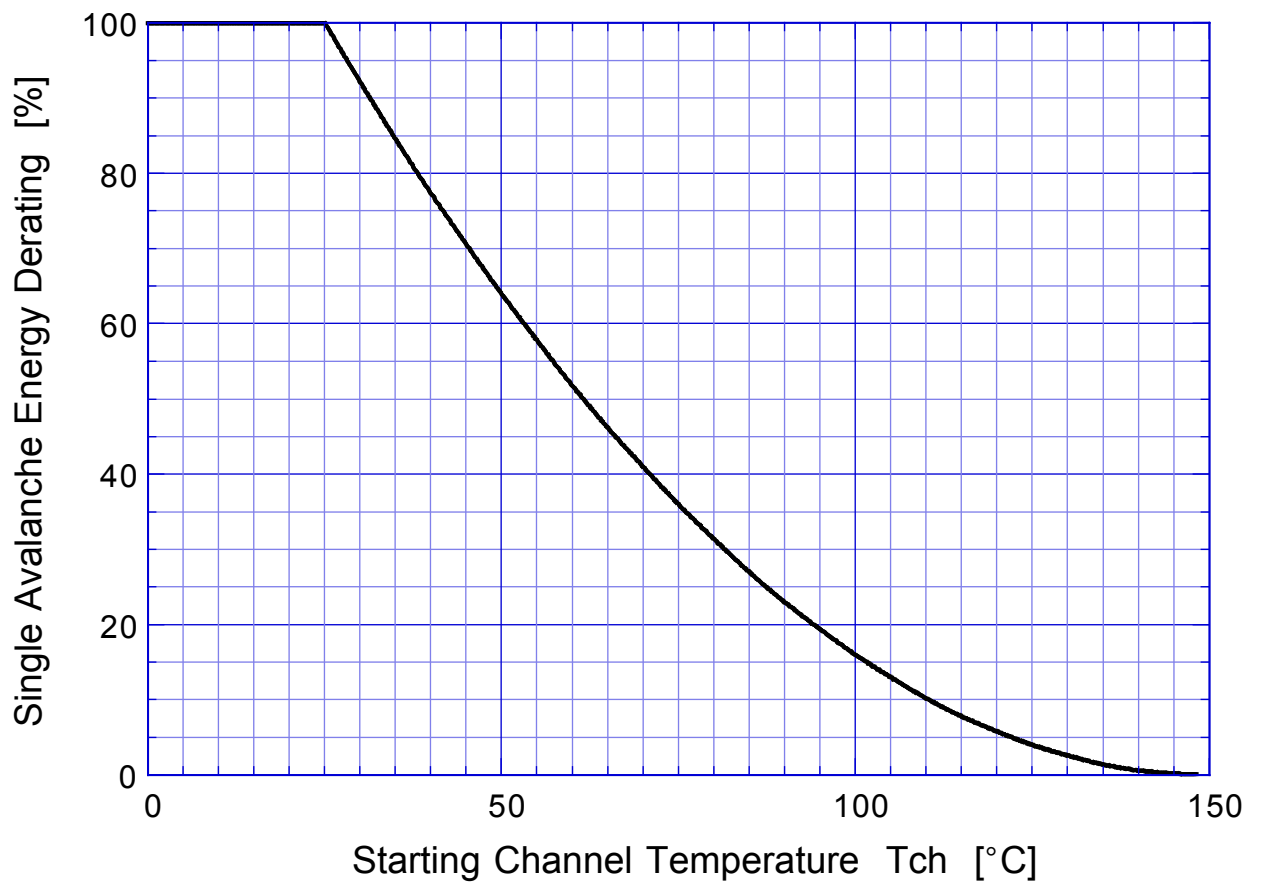
2SK2563 Safe Operating Area



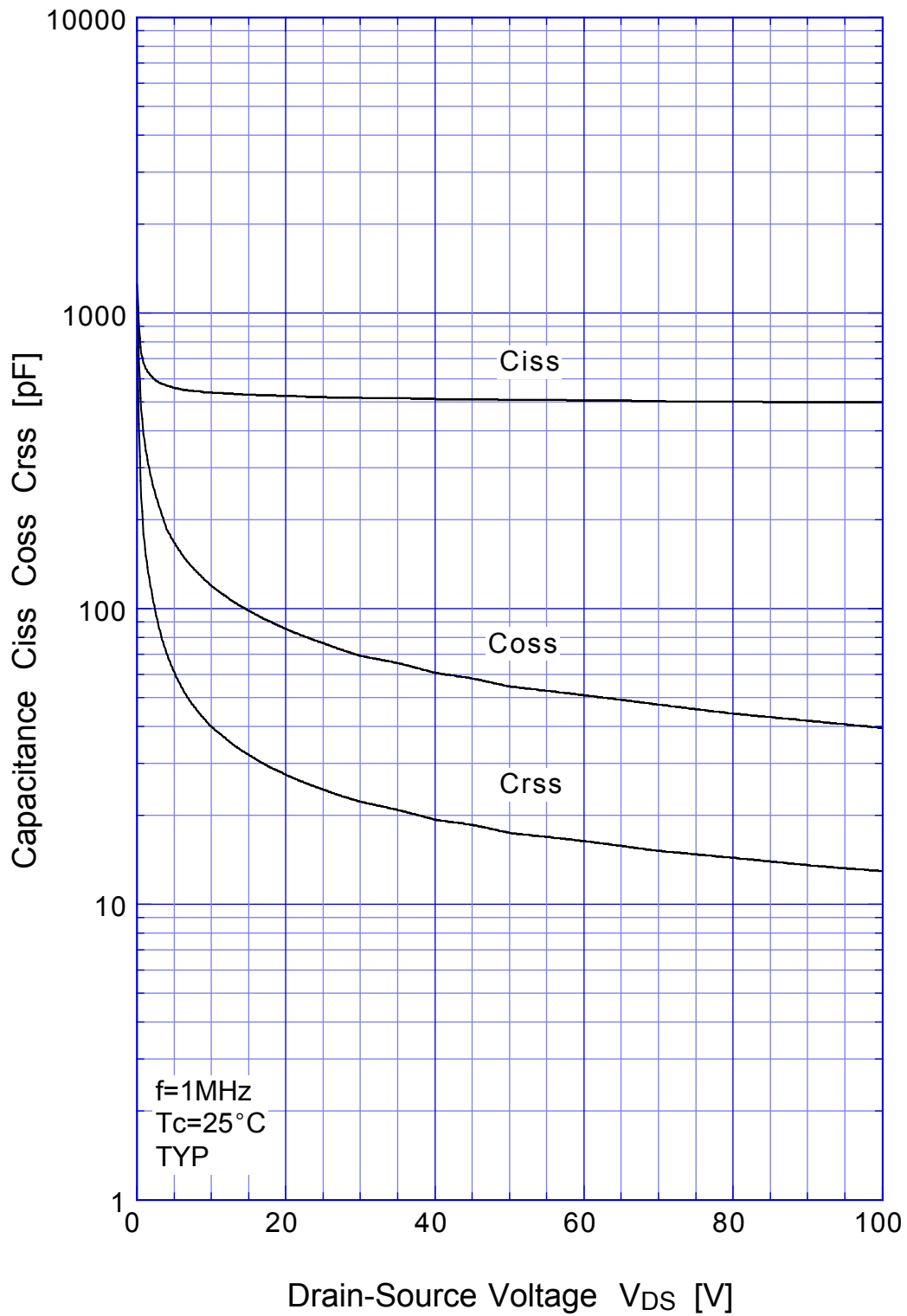
2SK2563 Transient Thermal Impedance



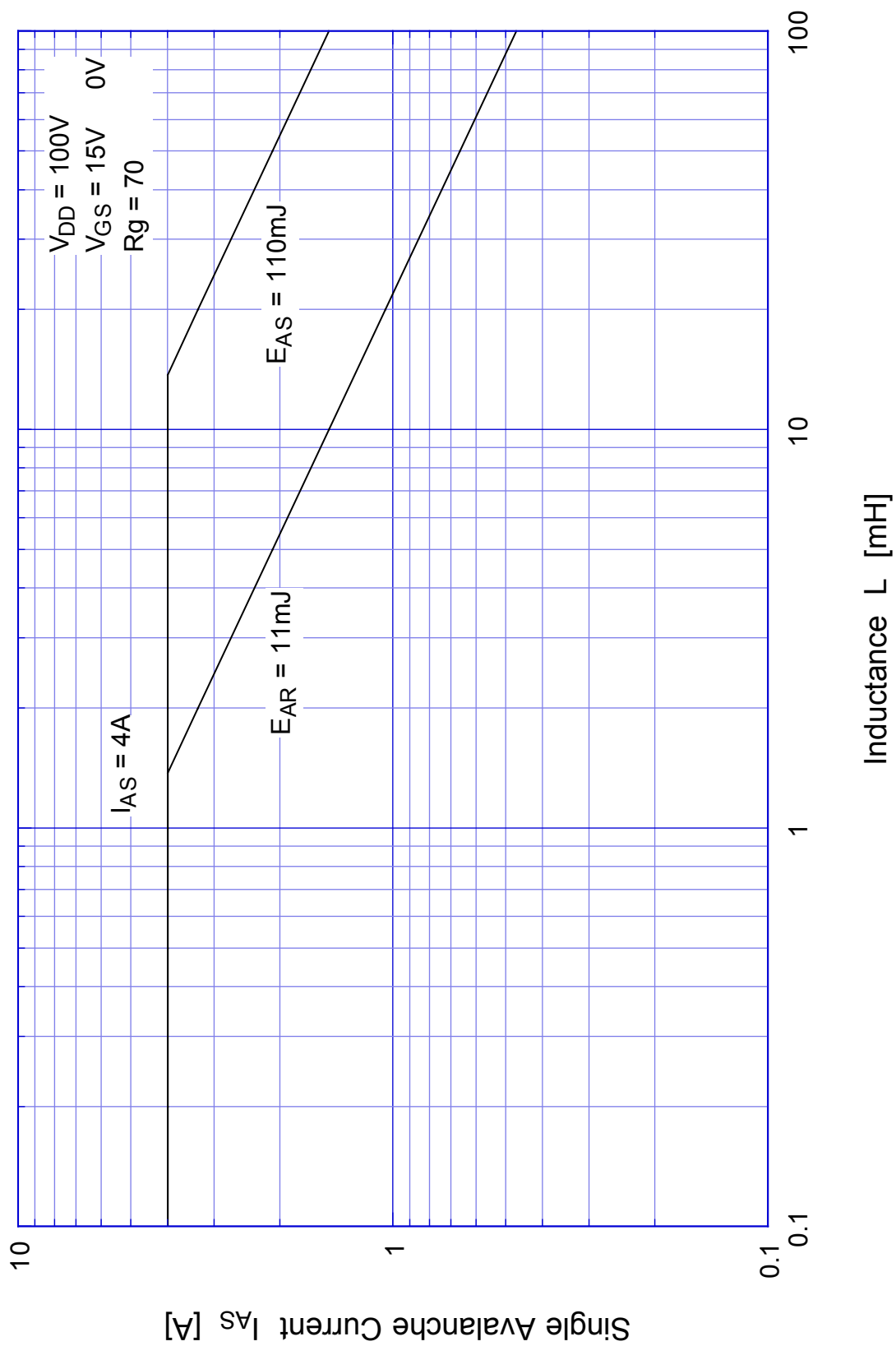
2SK2563 Single Avalanche Energy Derating



2SK2563 Capacitance

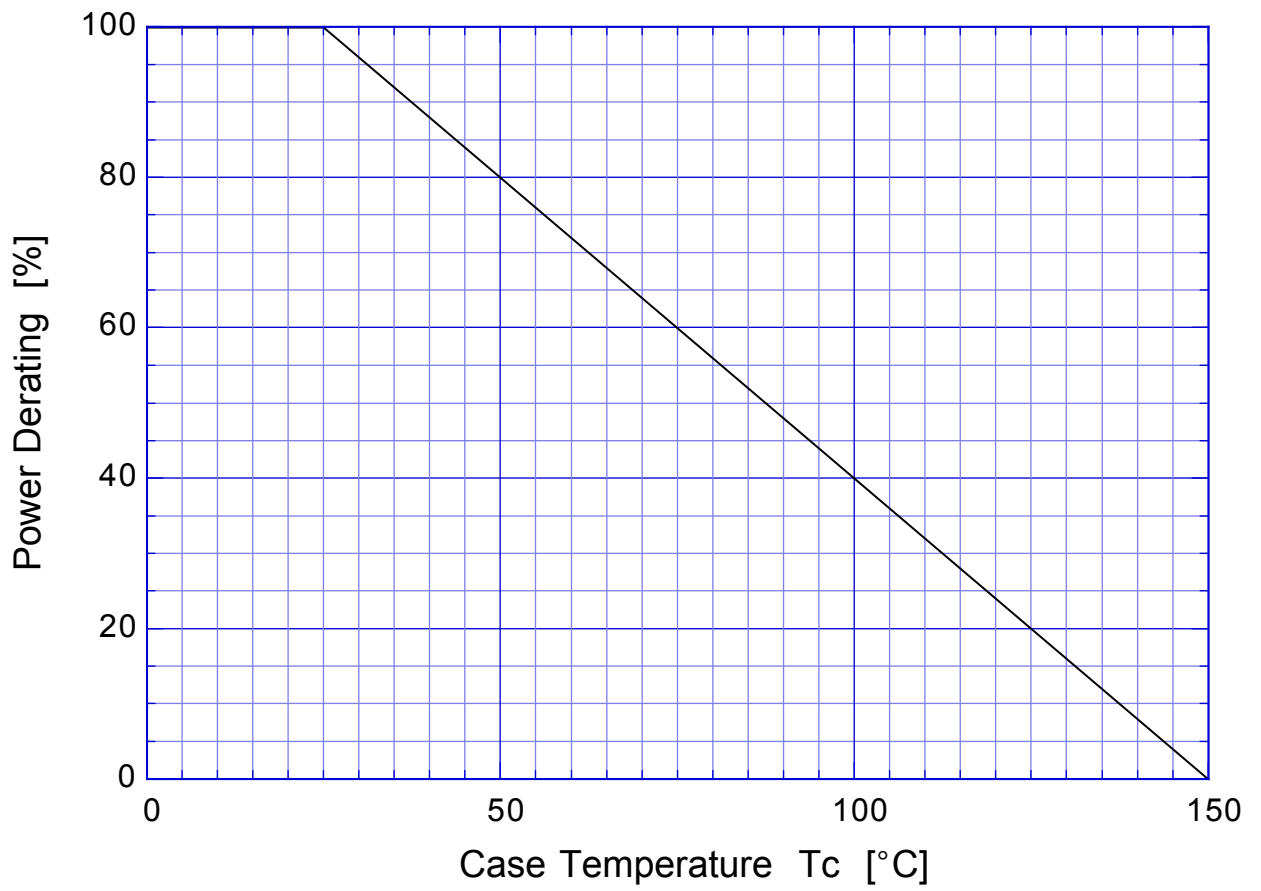


2SK2563 Single Avalanche Current - Inductive Load



2SK2563

Power Derating



2SK2563 Gate Charge Characteristics

